



### NCE N-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE30ND07S uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

V<sub>DS</sub> =30V,I<sub>D</sub> =7A

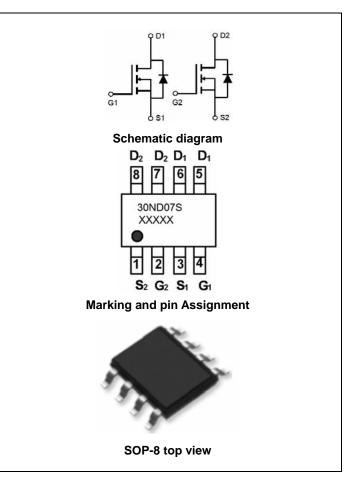
 $R_{DS(ON)}$  < 23m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)}$  < 40m $\Omega$  @  $V_{GS}$ =4.5V

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current

### **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



**Package Marking and Ordering Information** 

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30ND07S	NCE30ND07S	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T<sub>4</sub>=25 °C unless otherwise noted)

otiloi wioo ilotoa)		
Symbol	Limit	Unit
V <sub>DS</sub>	30	V
V <sub>GS</sub>	±20	V
I <sub>D</sub>	7	А
I <sub>D</sub> (100℃)	4.95	А
I <sub>DM</sub>	40	А
P <sub>D</sub>	2	W
$T_{J}$ , $T_{STG}$	-55 To 150	$^{\circ}\mathbb{C}$
	Symbol  VDS  VGS  ID  ID(100°C)  IDM  PD	Symbol         Limit           VDS         30           VGS         ±20           ID         7           ID(100°C)         4.95           IDM         40           PD         2

## **Thermal Characteristic**

Parameter	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	62.5	85	°C/W



# http://www.ncepower.com

Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•			•
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.1	-	2.1	V
Danie Course On Otata Basistana	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =7A	-	18	23 m(	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	25	40	mΩ
Forward Transconductance	<b>g</b> FS	$V_{DS}$ =5 $V$ , $I_{D}$ =7 $A$	-	15	-	S
Dynamic Characteristics (Note4)			•			•
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V, F=1.0MHz	-	380	-	PF
Output Capacitance	C <sub>oss</sub>		-	67	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	r-1.0Winz	-	41	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t <sub>d(on)</sub>		-	5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =15V, $R_L$ =2 $\Omega$	-	3	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS}$ =10 $V$ , $R_{G}$ =3 $\Omega$	-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg	\/ -15\/  -7A	-	7.2	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =15V, $I_{D}$ =7A, $V_{GS}$ =4.5V	-	1.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	VGS-4.5V	-	1.7	-	nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =7A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	7	Α

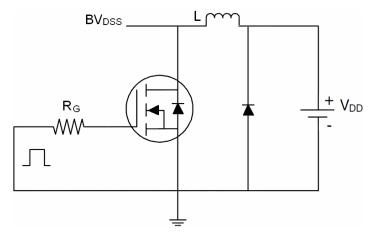
### Notes:

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. The value of R  $_{\text{BJA}}$  is measured with the device mounted on 1in  $^2$  FR-4 board with 2oz. Copper, in a still air environment with T  $_A$ =25°C. The value in any given application depends on the user's specific board design. Surface Mounted on FR4 Board, t  $\leq$  10 sec. The current rating is based on the t  $\leq$  10s thermal resistance rating.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production.

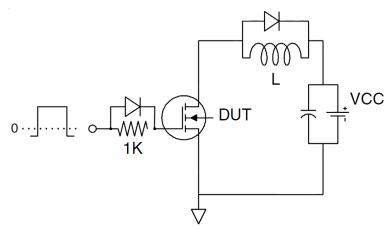


# **Test Circuit**

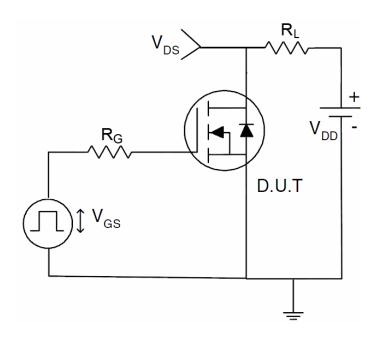
# 1) E<sub>AS</sub> Test Circuits



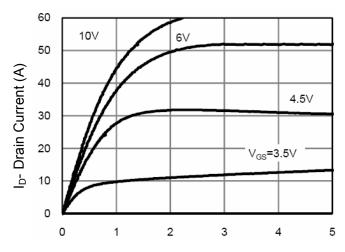
# 2) Gate Charge Test Circuit:



### 3) Switch Time Test Circuit:

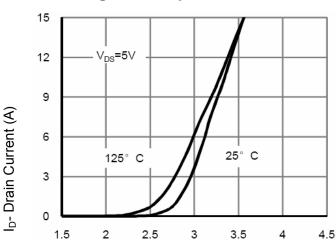


# Typical Electrical and Thermal Characteristics (Curves)



Vds Drain-Source Voltage (V)

**Figure 1 Output Characteristics** 



Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

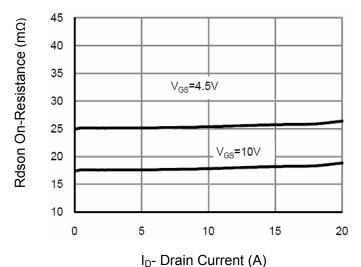


Figure 3 Rdson- Drain Current

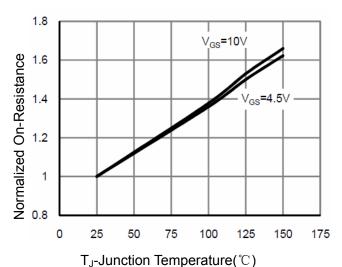
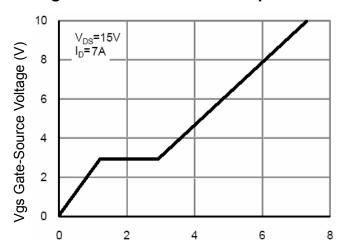


Figure 4 Rdson-JunctionTemperature



Qg Gate Charge (nC)
Figure 5 Gate Charge

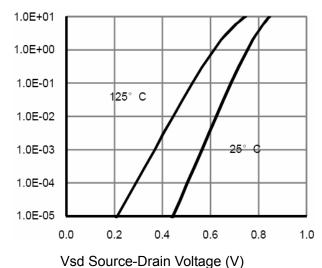


Figure 6 Source- Drain Diode Forward

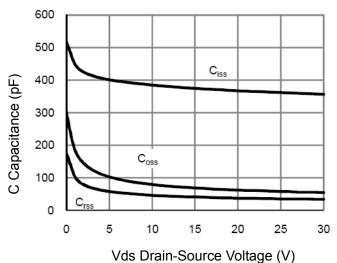
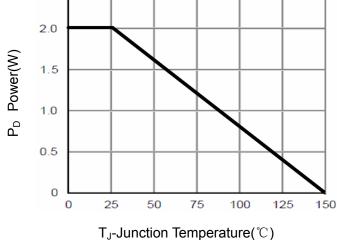
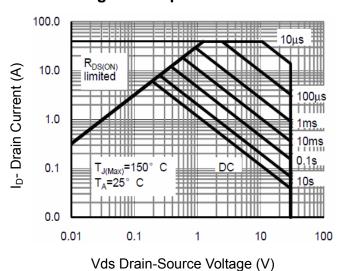


Figure 7 Capacitance vs Vds



2.5

T<sub>J</sub>-Junction remperature( C)



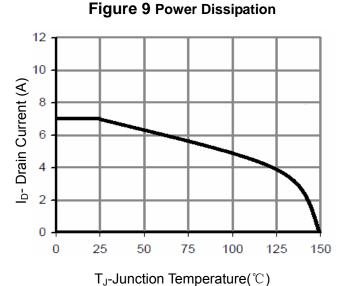
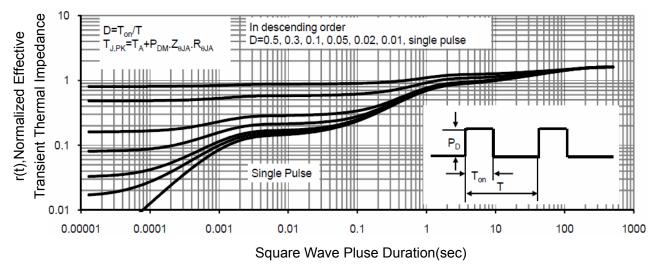


Figure 10 Current De-rating



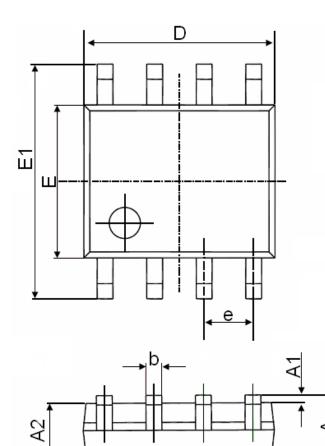


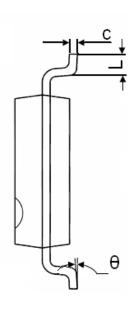
**Figure 11 Normalized Maximum Transient Thermal Impedance** 





# **SOP-8 Package Information**





Currele el	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
Е	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270(BSC)		0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	<b>0</b> °	8°	0°	8°	



### http://www.ncepower.com



### **Attention**

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.

单击下面可查看定价,库存,交付和生命周期等信息

>>NCEPOWER(无锡新洁能)